

**KSC3265**

**NPN EPITAXIAL SILICON TRANSISTOR**

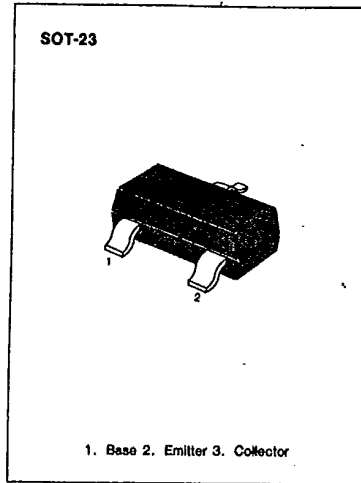
**LOW FREQUENCY AMPLIFIER**

• Complement to KSA1298

**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	30	V
Collector-Emitter Voltage	V <sub>CE0</sub>	25	V
Emitter-Base Voltage	V <sub>EB0</sub>	5	V
Collector Current	I <sub>c</sub>	800	mA
Base Current	I <sub>b</sub>	160	mA
Collector Dissipation	P <sub>C</sub>	200	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

• Refer to KSD261 for graphs



3

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>c</sub> = 10mA, I <sub>b</sub> = 0	25			V
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	I <sub>E</sub> = 1mA, I <sub>c</sub> = 0	5			V
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0			100	nA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = 5V, I <sub>c</sub> = 0			100	nA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = 1V, I <sub>c</sub> = 100mA	100		320	
	h <sub>FE2</sub>	V <sub>CE</sub> = 1V, I <sub>c</sub> = 800mA	40			
Collector Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 500mA, I <sub>b</sub> = 20mA			0.4	V
Base-Emitter On Voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = 1V, I <sub>c</sub> = 10mA	0.5		0.8	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 5V, I <sub>c</sub> = 10mA		120		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0 I = 1MHz		13		pF

**h<sub>FE</sub> (1) CLASSIFICATION**

Classification	O	Y
h <sub>FE</sub> (1)	100-200	160-320

